## NSN 5962-01-286-1614

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View Online at https://aerobasegroup.com/nsn/5962-01-286-1614

Body Length:
1.280 inches
Body Width:
Between 0.220 inches and 0.310 inches
Body Height:
Between 0.140 inches and 0.185 inches
Maximum Power Dissipation Rating:
1.04 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and burn in and programmable and bipolar and monolithic
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Bipolar metal-oxide semiconductor
Input Circuit Pattern:
14 input
Case Outline Source And Designator:
D-9 mil-m-38510
Current Rating Per Characteristic:
100.00 milliamperes output
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
-0.3 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
95.00 nanoseconds propagation delay time, low to high level output and 95.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Rom
Memory Capacity:
Unknown
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
24 printed circuit

N/a

Shelf Life:

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In	18	<i>(</i> )+	МЛО	201	ure:

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Demilitarization:

No

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